

Docket No.: 50432-657

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
MARK T. RAMSBEY, et al.	:	Confirmation Number:
	:	
Serial No.: Divisional of Appl. No.	:	
09/143,089	:	Group Art Unit:
	:	
Filed: November 25, 2003	:	Examiner:
	:	
For: METHODS AND ARRANGEMENTS FOR REDUCING FALSE PROGRAMMING IN		
NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES		

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 09/143,089, filed August 28, 1998, which is relied upon for an

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earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

A handwritten signature in black ink, appearing to read 'John A. Hankins', written over the printed name.

John A. Hankins  
Registration No. 32,029

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
(202) 756-8000 JAH:prg  
Facsimile: (202) 756-8087  
**Date: November 25, 2003**

SERIAL NO.  
Divisi nal of Appl. N .  
09/143,089

**FILING DATE**  
**November 25, 2003**

GROUP

(PTO-1449)

## U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)
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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		S. NAKAYAMA, "The effect of nitrogen in P + polysilicon gates on boron penetration into silicon substrate through the gate oxide", Symposium on VLSI technology Digest of Technical papers, pages 228-229, January 1996.
		T. KUROI et al., "Novel NICE (Nitrogen Implantation into CMOS Gate Electrode and Source-Drain) Structure for High Reliability and High Performance 0.25 um Dual Gate CMOS", IEDM, pages 325-328, January 1996.

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.